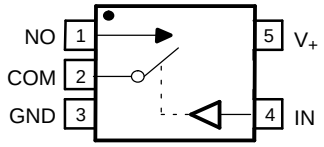
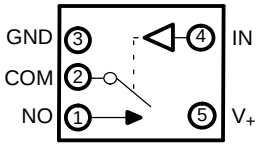
FEATURES

- **Low ON-State Resistance (10 Ω)**
- **Control Inputs Are 5.5-V Tolerant**
- **Low Charge Injection**
- **Low Total Harmonic Distortion (THD)**
- **1.65-V to 5.5-V Single-Supply Operation**
- **Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II**
- **ESD Performance Tested Per JESD 22**
  - **2000-V Human-Body Model (A114-B, Class II)**
  - **1000-V Charged-Device Model (C101)**

DBV OR DCK PACKAGE
(TOP VIEW)



YEP OR YZP PACKAGE
(BOTTOM VIEW)



DESCRIPTION/ORDERING INFORMATION

The TS5A1066 is a single-pole single-throw (SPST) analog switch that is designed to operate from 1.65 V to 5.5 V. This device can handle both digital and analog signals, and signals up to V_+ (peak) can be transmitted in either direction.

SUMMARY OF CHARACTERISTICS

Configuration	Single-Pole, Single-Throw Demultiplexer (1 × SPST)
Number of channels	1
ON-state resistance (r_{on})	7.5 Ω
ON-state resistance flatness ($r_{on(flat)}$)	2.5 Ω
Turn-on/turn-off time (t_{ON}/t_{OFF})	9.5 ns/2 ns
Charge injection (Q_C)	1 pC
Bandwidth (BW)	400 MHz
OFF isolation (O_{ISO})	–68 dB at 10 MHz
Total harmonic distortion (THD)	0.14%
Leakage current ($I_{COM(OFF)}$)	±0.1 μA
Power-supply current (I+)	0.05 μA
Package options	5-pin DSBGA, SOT-23, or SC-70

ORDERING INFORMATION

T_A	PACKAGE(1)		ORDERABLE PART NUMBER	TOP-SIDE MARKING(2)
–40°C to 85°C	NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump - YEP	Tape and reel	TS5A1066YEPR	JD_
	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Tape and reel	TS5A1066YZPR	
	SOT (SOT-23) – DBV	Tape and reel	TS5A1066DBVR	JAD_
	SOT (SC-70) – DCK	Tape and reel	TS5A1066DCKR	JD_

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.
(2) DBV/DCK: The actual top-side marking has one additional character that designates the assembly/test site.
YEP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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FUNCTION TABLE

IN	NO TO COM, COM TO NO
L	OFF
H	ON

Absolute Minimum and Maximum Rating(1)(2)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_+	Supply voltage range(3)		–0.5	6.5	V
V_{NO} V_{COM}	Analog voltage range(3)(4)(5)		–0.5	V_+ + 0.5	V
I_K	Analog port diode current	V_{NO}, V_{COM} < 0 or V_{NO}, V_{COM} > V_+	–50	50	mA
I_{NO} I_{COM}	On-state switch current	V_{NO}, V_{COM} = 0 to V_+	–50	50	mA
V_I	Digital input voltage range(3)(4)		–0.5	6.5	V
I_{IK}	Digital input clamp current	V_I < 0	–50		mA
I_+ I_{GND}	Continuous current through each V_+ or GND		–100	100	mA
θ_{JA}	Package thermal impedance(6)	DBV package		206	°C/W
		DCK package		252	
		YEP/YZP package		132	
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.
(3) All voltages are with respect to ground, unless otherwise specified.
(4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
(5) This value is limited to 5.5 V maximum.
(6) The package thermal impedance is calculated in accordance with JESD 51-7.

Electrical Characteristics for 5-V Supply(1)

V_+ = 4.5 V to 5.5 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}					0		V_+	V
ON-state resistance	r_{on}	$0 \le V_{NO} \le V_+$, I_{COM} = –30 mA,	Switch ON, See Figure 13	25°C	4.5 V		7.5	10	Ω
				Full				12	
ON-state resistance flatness	$r_{on(flat)}$	$0 \le V_{NO} \le V_+$, I_{COM} = –30 mA,	Switch ON, See Figure 13	25°C	4.5 V		2.5	5	Ω
				Full				6	
NO OFF leakage current	$I_{NO(OFF)}$	V_{NO} = 1 V, V_{COM} = 4.5 V, or V_{NO} = 4.5 V, V_{COM} = 1 V,	Switch OFF, See Figure 14	25°C	5.5 V	–0.2	0.1	0.2	µA
				Full		–2		2	
COM OFF leakage current	$I_{COM(OFF)}$	V_{COM} = 1 V, V_{NO} = 4.5 V, or V_{COM} = 4.5 V, V_{NO} = 1 V,	Switch OFF, See Figure 14	25°C	5.5 V	–0.1	0.05	0.1	µA
				Full		–0.2		0.2	
NO ON leakage current	$I_{NO(ON)}$	V_{NO} = 1 V, V_{COM} = Open, or V_{NO} = 4.5 V, V_{COM} = Open,	Switch ON, See Figure 15	25°C	5.5 V	–0.2	0.1	0.2	µA
				Full		–2		2	
COM ON leakage current	$I_{COM(ON)}$	V_{COM} = 1 V, V_{NO} = Open, or V_{COM} = 4.5 V, V_{NO} = Open,	Switch ON, See Figure 15	25°C	5.5 V	–0.1	0.05	0.1	µA
				Full		–0.2		0.2	
Digital Control Input (IN)									
Input logic high	V_{IH}			Full		$V_+ \times 0.7$		5.5	V
Input logic low	V_{IL}			Full		0		$V_+ \times 0.3$	V
Input leakage current	I_{IH}, I_{IL}	V_I = 5.5 V or 0		25°C	5.5 V	–0.1	0.05	0.1	µA
				Full		–1		1	

(1) The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.

Electrical Characteristics for 5-V Supply (continued)

V_+ = 4.5 V to 5.5 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t_{ON}	V_{COM} = 3 V, R_L = 300 Ω,	C_L = 35 pF, See Figure 17	25°C	5 V	3.5	4.8	5.5	ns
				Full	4.5 V to 5.5 V	3.5		7.5	
Turn-off time	t_{OFF}	V_{COM} = 3 V, R_L = 300 Ω,	C_L = 35 pF, See Figure 17	25°C	5 V	2	3	4.5	ns
				Full	4.5 V to 5.5 V	2		5.5	
Charge injection	Q_C	V_{GEN} = 0, C_L = 0.1 nF,	See Figure 20	25°C	5 V		1		pC
NO OFF capacitance	$C_{NO(OFF)}$	V_{NO} = V_+ or GND, Switch OFF,	See Figure 16	25°C	5 V		6.8		pF
COM OFF capacitance	$C_{COM(OFF)}$	V_{COM} = V_+ or GND, Switch OFF,	See Figure 16	25°C	5 V		6.8		pF
NO ON capacitance	$C_{NO(ON)}$	V_{NO} = V_+ or GND, Switch ON,	See Figure 16	25°C	5 V		14		pF
COM ON capacitance	$C_{COM(ON)}$	V_{COM} = V_+ or GND, Switch ON,	See Figure 16	25°C	5 V		14		pF
Digital input capacitance	C_I	V_I = V_+ or GND,	See Figure 16	25°C	5 V		2.2		pF
Bandwidth	BW	R_L = 50 Ω, Switch ON,	See Figure 18	25°C	5 V		400		MHz
OFF isolation	O_{ISO}	R_L = 50 Ω, f = 10 MHz,	Switch OFF, See Figure 19	25°C	5 V		–68		dB
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 21	25°C	5 V		0.14		%
Supply									
Positive supply current	I_+	V_I = V_+ or GND,	Switch ON or OFF	25°C	5.5 V		0.05	1	µA
				Full				5	

Electrical Characteristics for 3.3-V Supply(1)

V_+ = 3 V to 3.6 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}					0		V_+	V
ON-state resistance	r_{on}	$0 \le V_{NO} \le V_+$, I_{COM} = –24 mA,	Switch ON, See Figure 13	25°C	3 V		11.5	14	Ω
				Full				17	
ON-state resistance flatness	$r_{on(flat)}$	$0 \le V_{NO} \le V_+$, I_{COM} = –24 mA,	Switch ON, See Figure 13	25°C	3 V		5	10	Ω
				Full				12	
NO OFF leakage current	$I_{NO(OFF)}$	V_{NO} = 1 V, V_{COM} = 3 V, or V_{NO} = 3 V, V_{COM} = 1 V,	Switch OFF, See Figure 14	25°C	3.6 V	–0.2	0.1	0.2	µA
				Full		–2		2	
COM OFF leakage current	$I_{COM(OFF)}$	V_{COM} = 1 V, V_{NO} = 3 V, or V_{COM} = 3 V, V_{NO} = 1 V,	Switch OFF, See Figure 14	25°C	3.6 V	–0.1	0.05	0.1	µA
				Full		–0.2		0.2	
NO ON leakage current	$I_{NO(ON)}$	V_{NO} = 1 V, V_{COM} = Open, or V_{NO} = 3 V, V_{COM} = Open,	Switch ON, See Figure 15	25°C	3.6 V	–0.2	0.1	0.2	µA
				Full		–2		2	
COM ON leakage current	$I_{COM(ON)}$	V_{COM} = 1 V, V_{NO} = Open, or V_{COM} = 3 V, V_{NO} = Open,	Switch ON, See Figure 15	25°C	3.6 V	–0.1	0.05	0.1	µA
				Full		–0.2		0.2	
Digital Control Input (IN)									
Input logic high	V_{IH}			Full		$V_+ \times 0.7$		5.5	V
Input logic low	V_{IL}			Full		0		$V_+ \times 0.3$	V
Input leakage current	I_{IH}, I_{IL}	V_I = 5.5 V or 0		25°C	3.6 V	–0.1	0.05	0.1	µA
				Full		–1		1	

(1) The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.

Electrical Characteristics for 3.3-V Supply (continued)

V_+ = 3 V to 3.6 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t_{ON}	V_{COM} = 2 V, R_L = 300 Ω,	C_L = 35 pF, See Figure 17	25°C	3.3 V	4.5	5.5	8	ns
				Full	3 V to 3.6 V	4.5		8.5	
Turn-off time	t_{OFF}	V_{COM} = 2 V, R_L = 300 Ω,	C_L = 35 pF, See Figure 17	25°C	3.3 V	2	3	4.5	ns
				Full	3 V to 3.6 V	2		5.5	
Charge injection	Q_C	V_{GEN} = 0, C_L = 0.1 nF,	See Figure 20	25°C	3.3 V		1		pC
NO OFF capacitance	$C_{NO(OFF)}$	V_{NO} = V_+ or GND, Switch OFF,	See Figure 16	25°C	3.3 V		6.8		pF
COM OFF capacitance	$C_{COM(OFF)}$	V_{COM} = V_+ or GND, Switch OFF,	See Figure 16	25°C	3.3 V		6.8		pF
NO ON capacitance	$C_{NO(ON)}$	V_{NO} = V_+ or GND, Switch ON,	See Figure 16	25°C	3.3 V		14		pF
COM ON capacitance	$C_{COM(ON)}$	V_{COM} = V_+ or GND, Switch ON,	See Figure 16	25°C	3.3 V		14		pF
Digital input capacitance	C_I	V_I = V_+ or GND,	See Figure 16	25°C	3.3 V		2.2		pF
Bandwidth	BW	R_L = 50 Ω, Switch ON,	See Figure 18	25°C	3.3 V		400		MHz
OFF isolation	O_{ISO}	R_L = 50 Ω, f = 10 MHz,	Switch OFF, See Figure 19	25°C	3.3 V		–68		dB
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 21	25°C	3.3 V		0.2		%
Supply									
Positive supply current	I_+	V_I = V_+ or GND,	Switch ON or OFF	25°C	3.6 V		0.05	1	μA
				Full				5	

Electrical Characteristics for 2.5-V Supply(1)

V_+ = 2.3 V to 2.7 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}					0		V_+	V
ON-state resistance	r_{on}	$0 \le V_{NO} \le V_+$, I_{COM} = –8 mA,	Switch ON, See Figure 13	25°C	2.3 V		20	24	Ω
				Full				27	
ON-state resistance flatness	$r_{on(flat)}$	$0 \le V_{NO} \le V_+$, I_{COM} = –8 mA,	Switch ON, See Figure 13	25°C	2.3 V		7.5	15	Ω
				Full				20	
NO OFF leakage current	$I_{NO(OFF)}$	V_{NO} = 0.5 V, V_{COM} = 2.2 V, or V_{NO} = 2.2 V, V_{COM} = 0.5 V,	Switch OFF, See Figure 14	25°C	2.7 V	–0.2	0.1	0.2	µA
				Full		–2		2	
COM OFF leakage current	$I_{COM(OFF)}$	V_{COM} = 0.5 V, V_{NO} = 2.2 V, or V_{COM} = 2.2 V, V_{NO} = 0.5 V,	Switch OFF, See Figure 14	25°C	2.7 V	–0.1	0.05	0.1	µA
				Full		–0.2		0.2	
NO ON leakage current	$I_{NO(ON)}$	V_{NO} = 0.5 V, V_{COM} = Open, or V_{NO} = 2.2 V, V_{COM} = Open,	Switch ON, See Figure 15	25°C	2.7 V	–0.2	0.1	0.2	µA
				Full		–2		2	
COM ON leakage current	$I_{COM(ON)}$	V_{COM} = 0.5 V, V_{NO} = Open, or V_{COM} = 2.2 V, V_{NO} = Open,	Switch ON, See Figure 15	25°C	2.7 V	–0.1	0.05	0.1	µA
				Full		–0.2		0.2	
Digital Control Input (IN)									
Input logic high	V_{IH}			Full		$V_+ \times 0.7$		5.5	V
Input logic low	V_{IL}			Full		0		$V_+ \times 0.3$	V
Input leakage current	I_{IH}, I_{IL}	V_I = 5.5 V or 0		25°C	2.7 V	–0.1	0.05	0.1	µA
				Full		–1		1	

(1) The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.

Electrical Characteristics for 2.5-V Supply (continued)

V_+ = 2.3 V to 2.7 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t_{ON}	V_{COM} = 1.5 V, R_L = 300 Ω,	C_L = 35 pF, See Figure 17	25°C	2.5 V	4.5	5.5	8	ns
				Full	2.3 V to 2.7 V	4.5		8.5	
Turn-off time	t_{OFF}	V_{COM} = 1.5 V, R_L = 300 Ω,	C_L = 35 pF, See Figure 17	25°C	2.5 V	1.5	2.5	4	ns
				Full	2.3 V to 2.7 V	1.5		5.5	
Charge injection	Q_C	V_{GEN} = 0, C_L = 0.1 nF,	See Figure 20	25°C	2.5 V		1		pC
NO OFF capacitance	$C_{NO(OFF)}$	V_{NO} = V_+ or GND, Switch OFF,	See Figure 16	25°C	2.5 V		6.8		pF
COM OFF capacitance	$C_{COM(OFF)}$	V_{COM} = V_+ or GND, Switch OFF,	See Figure 16	25°C	2.5 V		6.8		pF
NO ON capacitance	$C_{NO(ON)}$	V_{NO} = V_+ or GND, Switch ON,	See Figure 16	25°C	2.5 V		14		pF
COM ON capacitance	$C_{COM(ON)}$	V_{COM} = V_+ or GND, Switch ON,	See Figure 16	25°C	2.5 V		14		pF
Digital input capacitance	C_I	V_I = V_+ or GND,	See Figure 16	25°C	2.5 V		2.2		pF
Bandwidth	BW	R_L = 50 Ω, Switch ON,	See Figure 18	25°C	2.5 V		400		MHz
OFF isolation	O_{ISO}	R_L = 50 Ω, f = 10 MHz,	Switch OFF, See Figure 19	25°C	2.5 V		–68		dB
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 21	25°C	2.5 V		0.32		%
Supply									
Positive supply current	I_+	V_I = V_+ or GND,	Switch ON or OFF	25°C	2.7 V		0.05	1	μA
				Full				5	

Electrical Characteristics for 1.8-V Supply(1)

V_+ = 1.65 V to 1.95 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range	V_{COM}, V_{NO}					0		V_+	V
ON-state resistance	r_{on}	0 ≤ V_{NO} ≤ V_+, I_{COM} = –4 mA,	Switch ON, See Figure 13	25°C	1.65 V		74.5	80	Ω
				Full				100	
ON-state resistance flatness	$r_{on(flat)}$	0 ≤ V_{NO} ≤ V_+, I_{COM} = –4 mA,	Switch ON, See Figure 13	25°C	1.65 V		64.5	70	Ω
				Full				90	
NO OFF leakage current	$I_{NO(OFF)}$	V_{NO} = 0.3 V, V_{COM} = 1.65 V, or V_{NO} = 1.65 V, V_{COM} = 0.3 V,	Switch OFF, See Figure 14	25°C	1.95 V	–0.2	0.1	0.2	µA
				Full		–2		2	
COM OFF leakage current	$I_{COM(OFF)}$	V_{COM} = 0.3 V, V_{NO} = 1.65 V, or V_{COM} = 1.65 V, V_{NO} = 0.3 V,	Switch OFF, See Figure 14	25°C	1.95 V	–0.1	0.05	0.1	µA
				Full		–0.2		0.2	
NO ON leakage current	$I_{NO(ON)}$	V_{NO} = 0.3 V, V_{COM} = Open, or V_{NO} = 1.65 V, V_{COM} = Open,	Switch ON, See Figure 15	25°C	1.95 V	–0.2	0.1	0.2	µA
				Full		–2		2	
COM ON leakage current	$I_{COM(ON)}$	V_{COM} = 0.3 V, V_{NO} = Open, or V_{COM} = 1.65 V, V_{NO} = Open,	Switch ON, See Figure 15	25°C	1.95 V	–0.1	0.05	0.1	µA
				Full		–0.2		0.2	
Digital Control Input (IN)									
Input logic high	V_{IH}			Full		$V_+ \times 0.65$		5.5	V
Input logic low	V_{IL}			Full		0		$V_+ \times 0.35$	V
Input leakage current	I_{IH}, I_{IL}	V_I = 5.5 V or 0		25°C	1.95 V	–0.1	0.05	0.1	µA
				Full		–1		1	

(1) The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.

Electrical Characteristics for 1.8-V Supply (continued)

V_+ = 1.65 V to 1.95 V, T_A = –40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	V_+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	t_{ON}	V_{COM} = 1.3 V, R_L = 300 Ω,	C_L = 35 pF, See Figure 17	25°C	1.8 V	9.5	10	12	ns
				Full	1.65 V to 1.95 V	8.5		13	
Turn-off time	t_{OFF}	V_{COM} = 1.3 V, R_L = 300 Ω,	C_L = 35 pF, See Figure 17	25°C	1.8 V	1.5	2	4	ns
				Full	1.65 V to 1.95 V	1.5		5.5	
Charge injection	Q_C	V_{GEN} = 0, C_L = 0.1 nF,	See Figure 20	25°C	1.8 V		1		pC
NO OFF capacitance	$C_{NO(OFF)}$	V_{NO} = V_+ or GND, Switch OFF,	See Figure 16	25°C	1.8 V		6.8		pF
COM OFF capacitance	$C_{COM(OFF)}$	V_{COM} = V_+ or GND, Switch OFF,	See Figure 16	25°C	1.8 V		6.8		pF
NO ON capacitance	$C_{NO(ON)}$	V_{NO} = V_+ or GND, Switch ON,	See Figure 16	25°C	1.8 V		14		pF
COM ON capacitance	$C_{COM(ON)}$	V_{COM} = V_+ or GND, Switch ON,	See Figure 16	25°C	1.8 V		14		pF
Digital input capacitance	C_I	V_I = V_+ or GND,	See Figure 16	25°C	1.8 V		2.2		pF
Bandwidth	BW	R_L = 50 Ω, Switch ON,	See Figure 18	25°C	1.8 V		400		MHz
OFF isolation	O_{ISO}	R_L = 50 Ω, f = 10 MHz,	Switch OFF, See Figure 19	25°C	1.8 V		–68		dB
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 50 pF,	f = 20 Hz to 20 kHz, See Figure 21	25°C	1.8 V		0.32		%
Supply									
Positive supply current	I_+	V_I = V_+ or GND,	Switch ON or OFF	25°C	1.95 V		0.05	1	μA
				Full				5	

TYPICAL PERFORMANCE

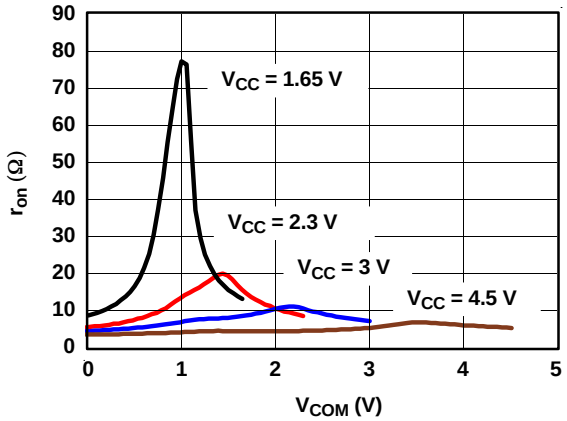


Figure 1. r_{on} vs V_{COM}

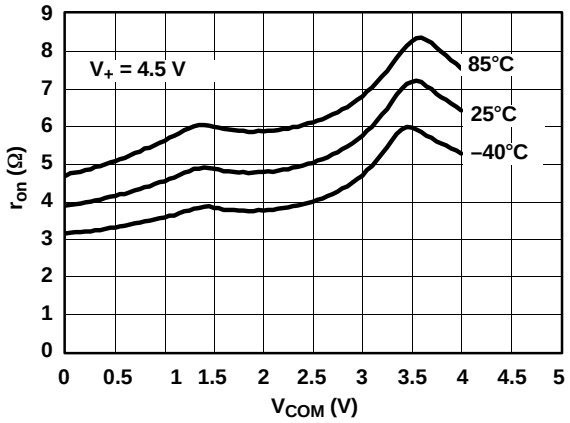


Figure 2. r_{on} vs V_{COM} (V_+ = 3 V)

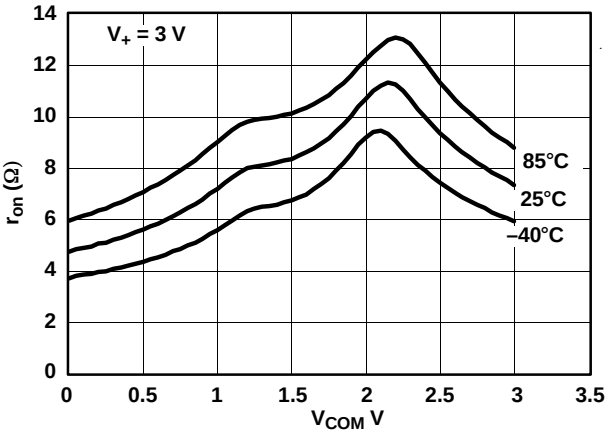


Figure 3. r_{on} vs V_{COM} (V_+ = 5 V)

TYPICAL PERFORMANCE

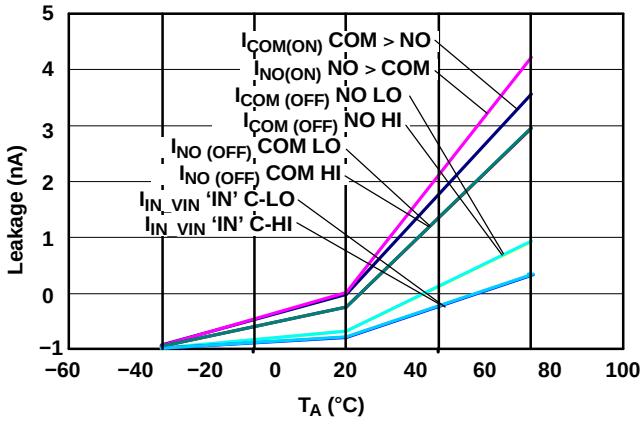


Figure 4. Leakage Current vs Temperature (V_+ = 5.5 V)

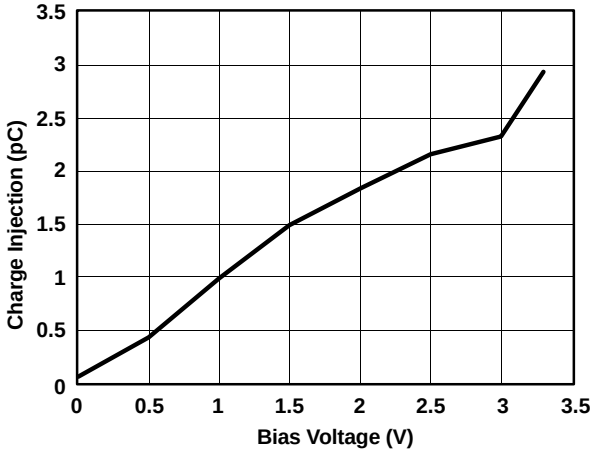


Figure 5. Charge Injection (Q_C) vs Bias Voltage

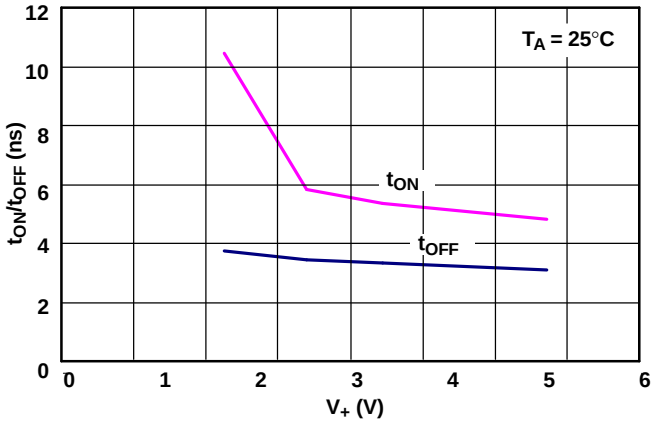


Figure 6. t_{ON} and t_{OFF} vs Supply Voltage

TYPICAL PERFORMANCE

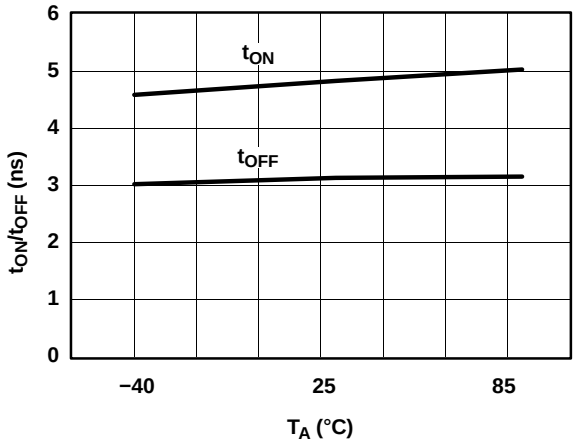


Figure 7. t_{ON} and t_{OFF} vs Temperature (V_+ = 5 V)

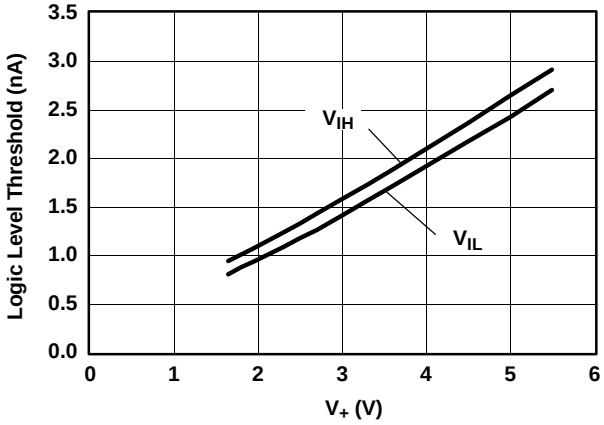


Figure 8. Logic-Level Threshold vs V_+

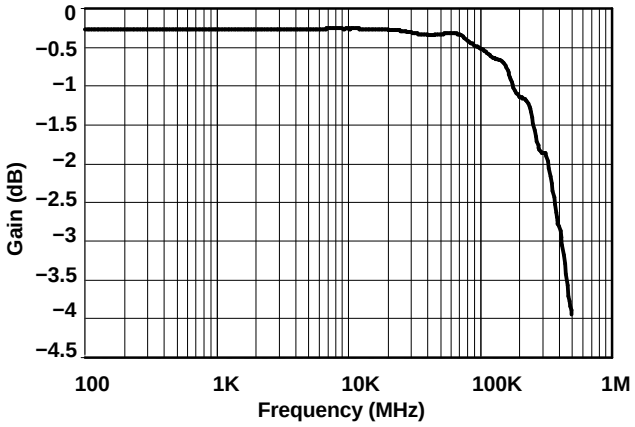


Figure 9. Bandwidth (V_+ = 5 V)

TYPICAL PERFORMANCE

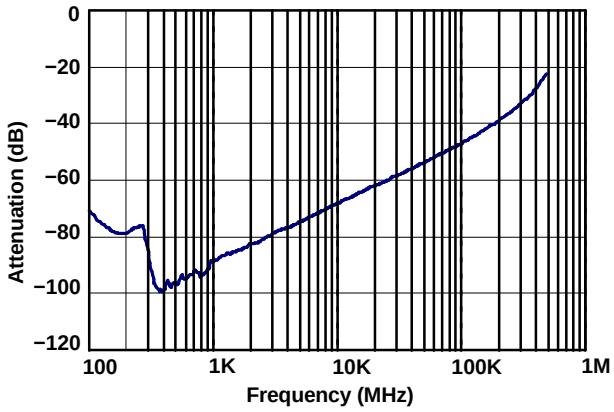


Figure 10. OFF Isolation (V_+ = 5 V)

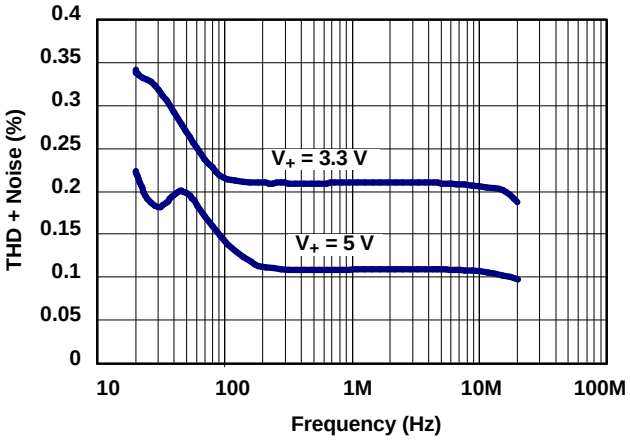


Figure 11. Total Harmonic Distortion vs Frequency

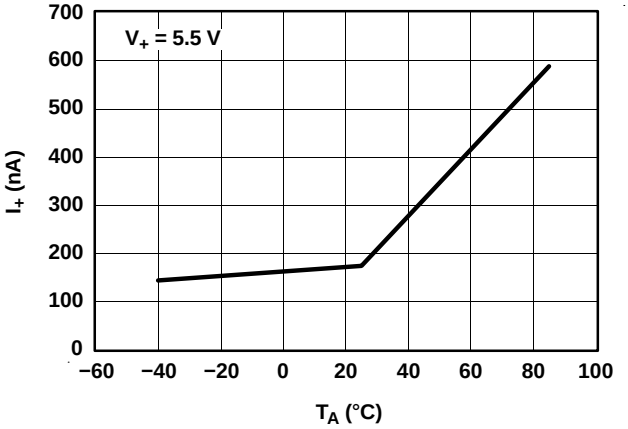


Figure 12. Power-Supply Current vs Temperature (V_+ = 5 V)

PIN DESCRIPTION

PIN	NAME	DESCRIPTION
1	NO	Normally open
2	COM	Common
3	GND	Digital ground
4	IN	Digital control to connect COM to NO
5	V_+	Power supply

PARAMETER DESCRIPTION

SYMBOL	DESCRIPTION
V_{COM}	Voltage at COM
V_{NO}	Voltage at NO
r_{on}	Resistance between COM and NO ports when the channel is ON
$r_{on(flat)}$	Difference between the maximum and minimum value of ron in a channel over the specified range of conditions
$I_{NO(OFF)}$	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state
$I_{NO(ON)}$	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) open
$I_{COM(OFF)}$	Leakage current measured at the COM port, with the corresponding channel (COM to NO) in the OFF state
$I_{COM(ON)}$	Leakage current measured at the COM port, with the corresponding channel (COM to NO) in the ON state and the output (NO) open
V_{IH}	Minimum input voltage for logic high for the control input (IN)
V_{IL}	Maximum input voltage for logic low for the control input (IN)
V_I	Voltage at the control input (IN)
I_{IH}, I_{IL}	Leakage current measured at the control input (IN)
t_{ON}	Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM or NO) signal when the switch is turning ON.
t_{OFF}	Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM or NO) signal when the switch is turning OFF.
Q_C	Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NO or COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input.Charge injection, $Q_C = C_L \times \Delta V_{COM}$, C_L is the load capacitance and ΔV_{COM} is the change in analog output voltage.
$C_{NO(OFF)}$	Capacitance at the NO port when the corresponding channel (NO to COM) is OFF
$C_{NO(ON)}$	Capacitance at the NO port when the corresponding channel (NO to COM) is ON
$C_{COM(OFF)}$	Capacitance at the COM port when the corresponding channel (COM to NO) is OFF
$C_{COM(ON)}$	Capacitance at the COM port when the corresponding channel (COM to NO) is ON
C_I	Capacitance of IN
O_{ISO}	OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NO to COM) in the OFF state.
BW	Bandwidth of the switch. This is the frequency in which the gain of an ON channel is -3 dB below the DC gain.
THD	Total harmonic distortion is defined as the ratio of the root mean square (RMS) value of the second, third, and higher harmonics to the magnitude of fundamental harmonic.
I_+	Static power-supply current with the control (IN) pin at V_+ or GND
ΔI_+	This is the increase in I_+ for each control (IN) input that is at the specified voltage, rather than at V_+ or GND.

PARAMETER MEASUREMENT INFORMATION

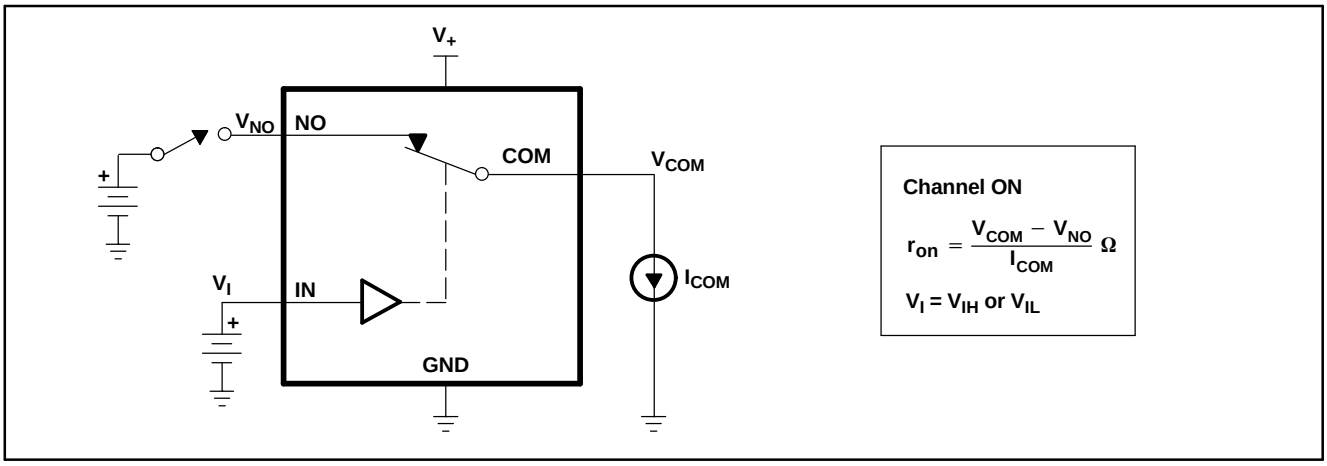


Figure 13. ON-State Resistance (r_{on})

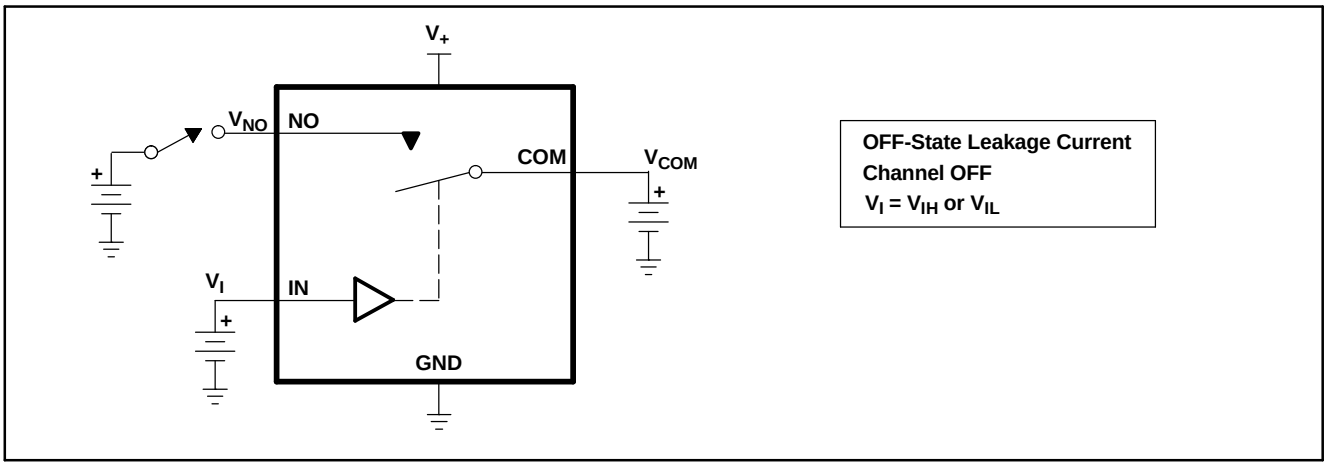


Figure 14. OFF-State Leakage Current ($I_{COM(OFF)}$, $I_{NO(OFF)}$)

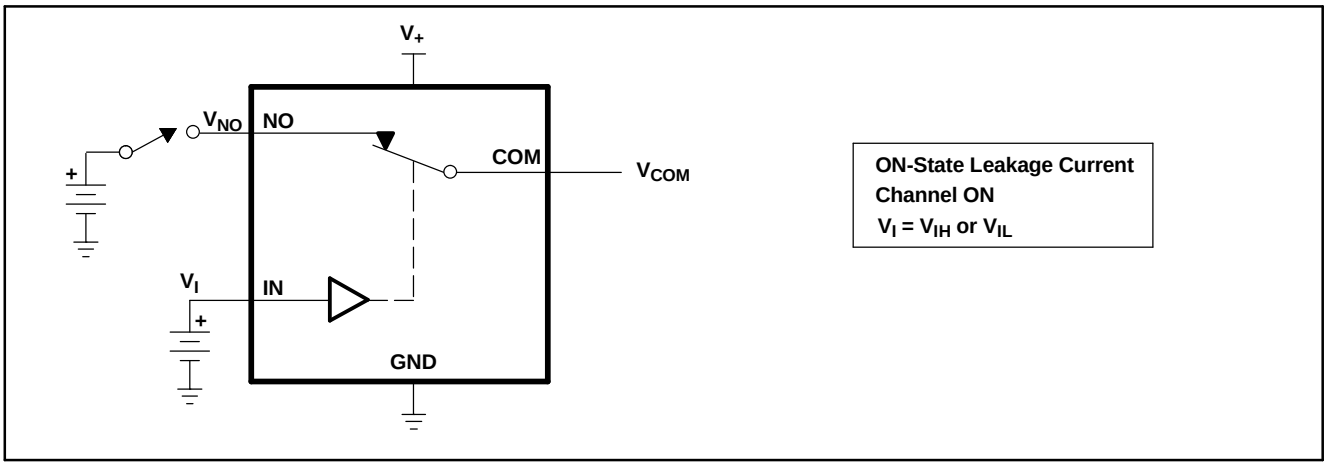


Figure 15. ON-State Leakage Current ($I_{COM(ON)}$, $I_{NO(ON)}$)

PARAMETER MEASUREMENT INFORMATION (continued)

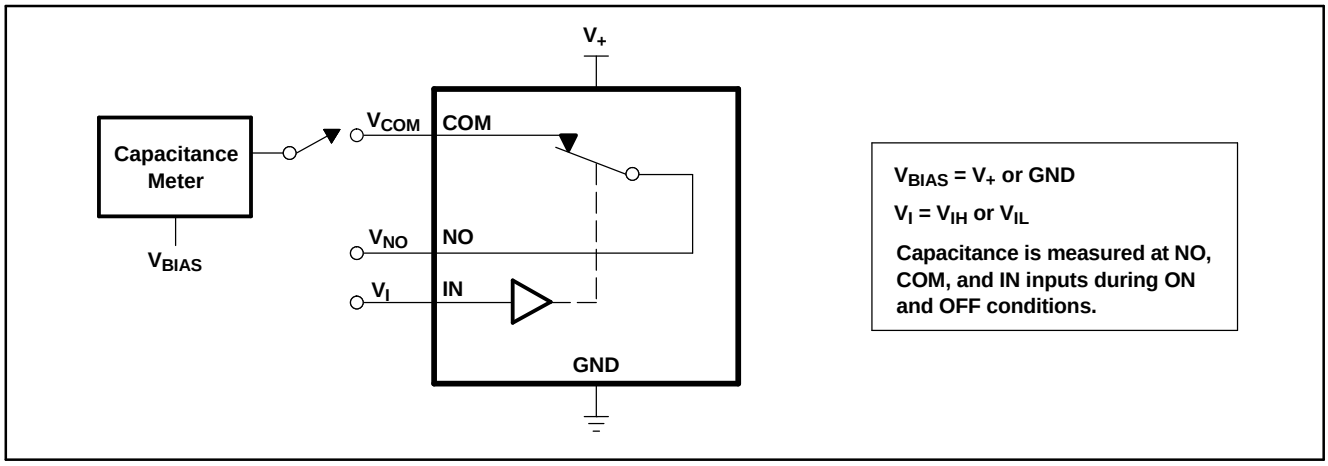
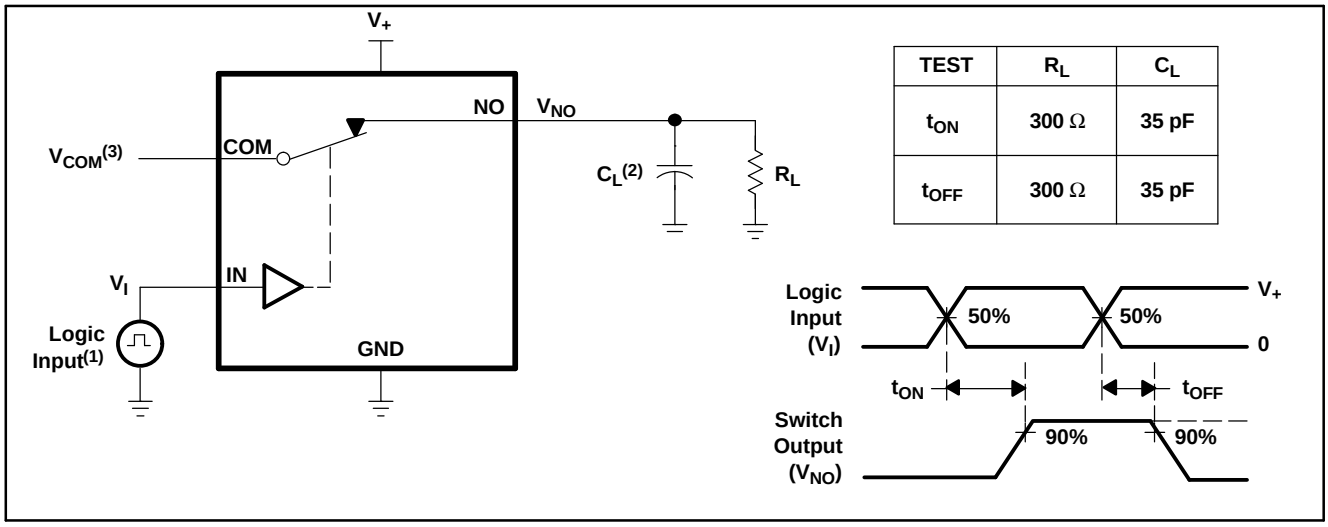


Figure 16. Capacitance (C_I, $C_{COM(OFF)}$, $C_{COM(ON)}$, $C_{NO(OFF)}$, $C_{NO(ON)}$)



(1) All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.
(2) C_L includes probe and jig capacitance.
(3) See Electrical Characteristics for V_{COM}.

Figure 17. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})

PARAMETER MEASUREMENT INFORMATION (continued)

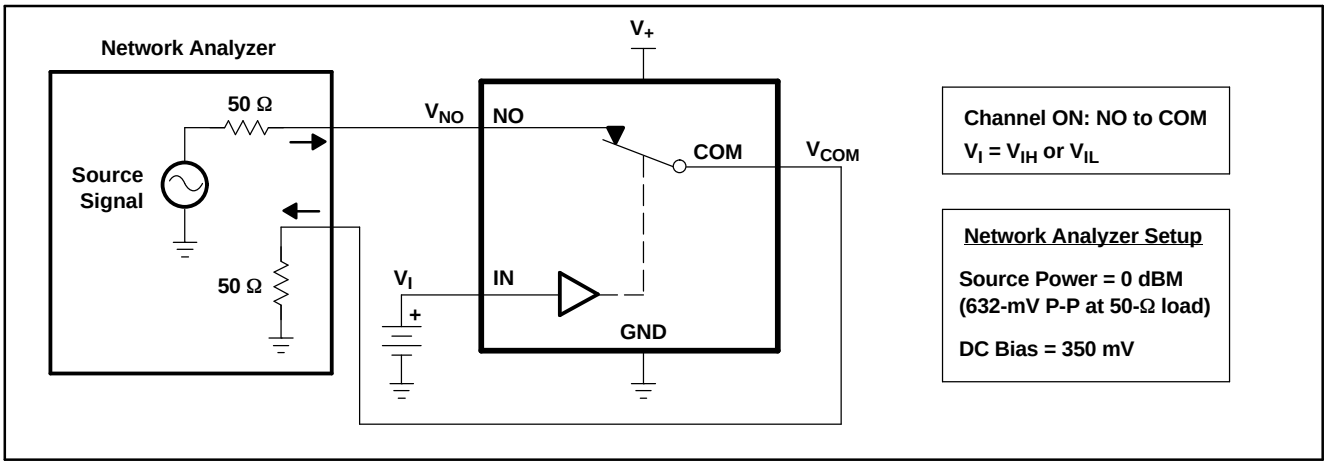


Figure 18. Bandwidth (BW)

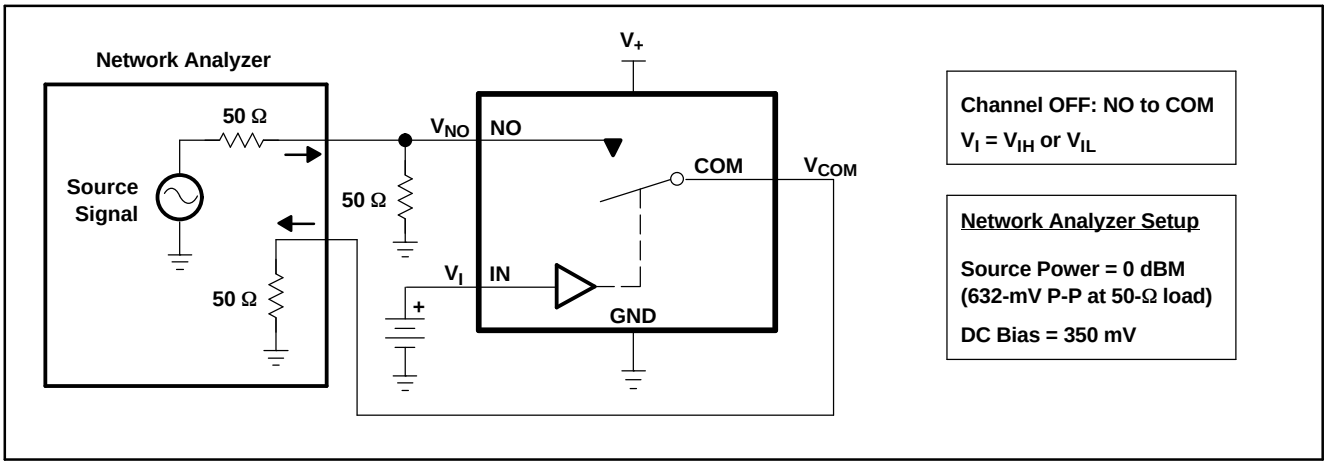
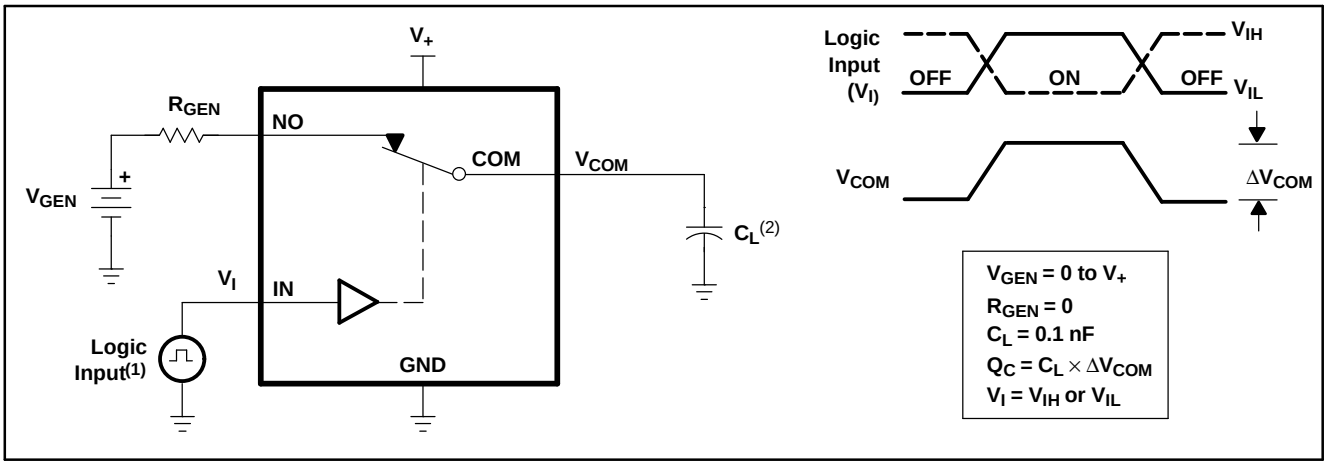


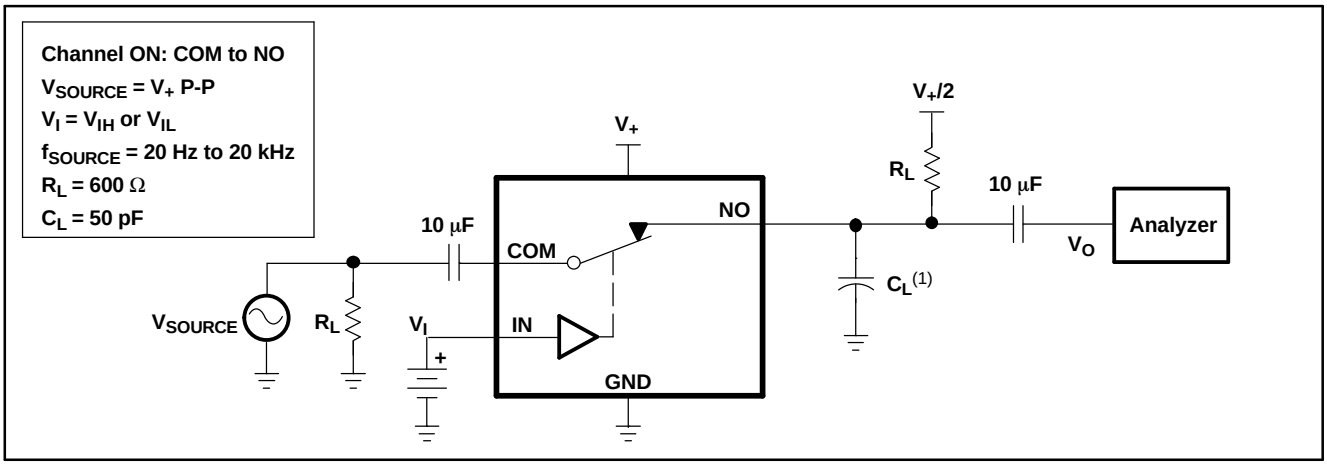
Figure 19. OFF Isolation (O_{ISO})

PARAMETER MEASUREMENT INFORMATION (continued)



(1) All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.
(2) C_L includes probe and jig capacitance.

Figure 20. Charge Injection (Q_C)



(1) C_L includes probe and jig capacitance.

Figure 21. Total Harmonic Distortion (THD)

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)
TS5A1066DBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS5A1066DBVRE4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS5A1066DBVRG4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS5A1066DCKR	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS5A1066DCKRE4	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS5A1066DCKRG4	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS5A1066YZPR	ACTIVE	DSBGA	YZP	5	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

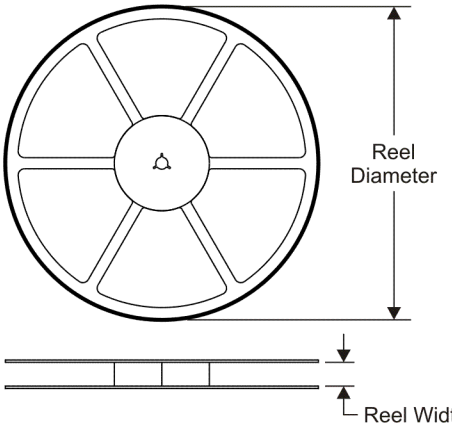
(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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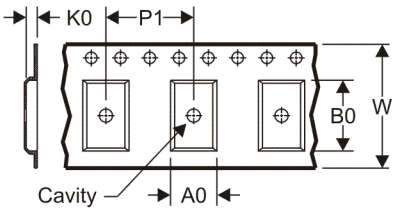
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TAPE AND REEL INFORMATION

REEL DIMENSIONS

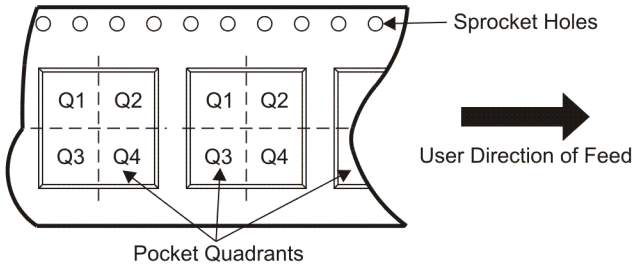


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

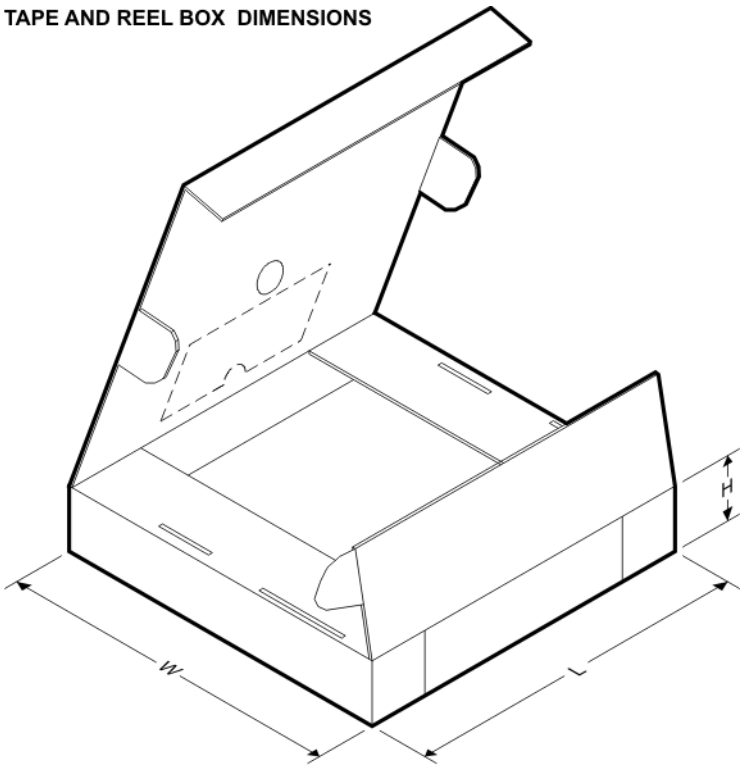
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A1066YZPR	DSBGA	YZP	5	3000	180.0	8.4	1.02	1.52	0.63	4.0	8.0	Q1

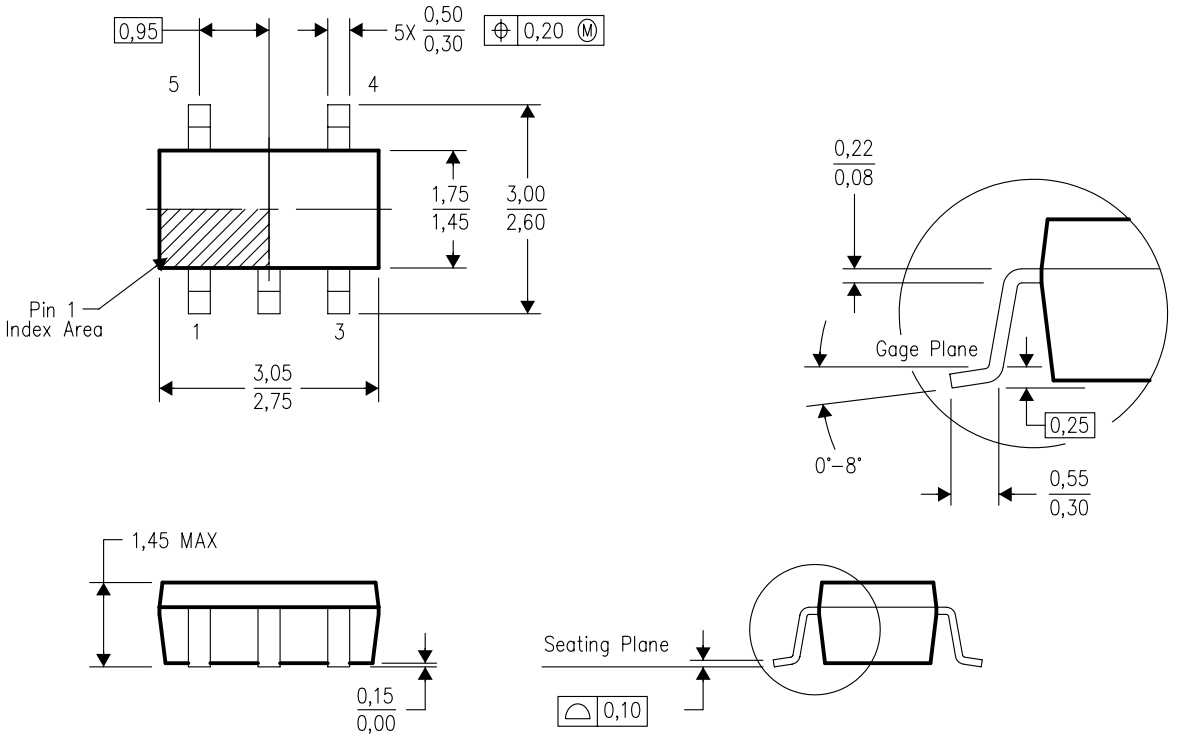
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A1066YZPR	DSBGA	YZP	5	3000	220.0	220.0	34.0

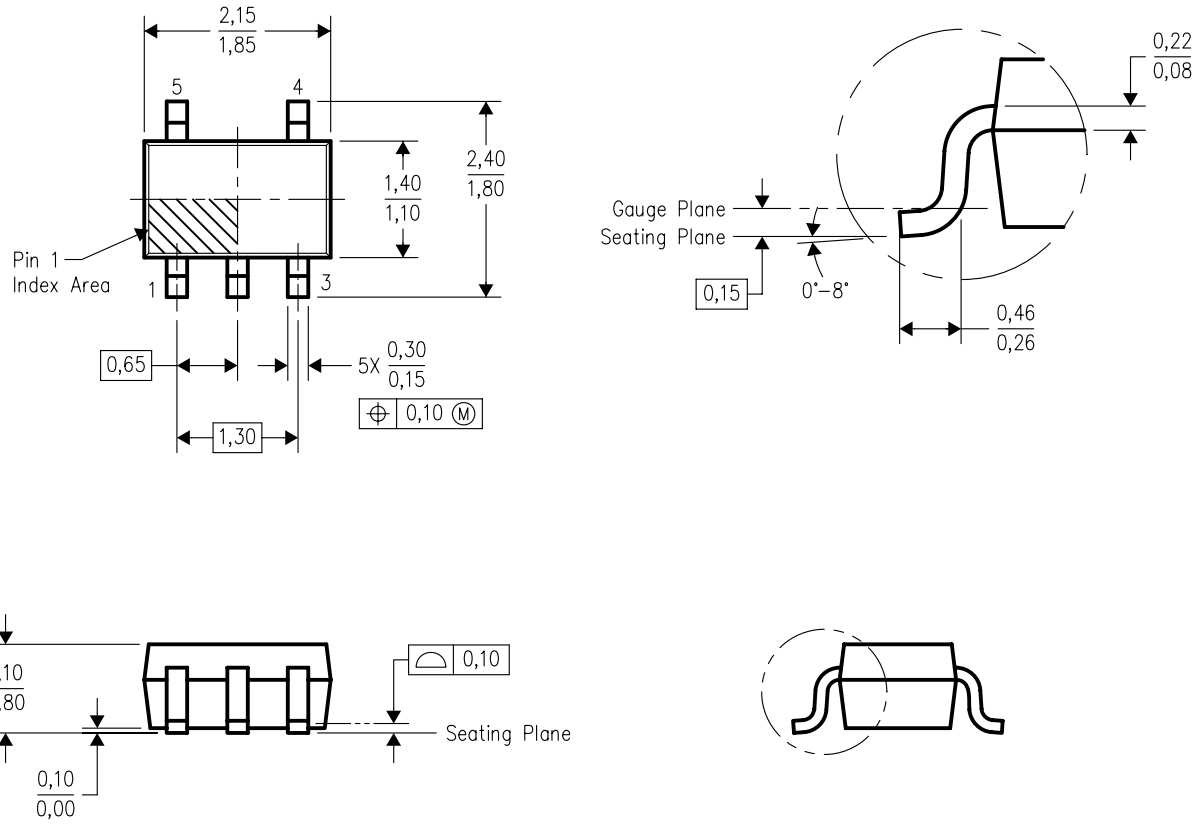
DBV (R–PDSO–G5) PLASTIC SMALL–OUTLINE PACKAGE



4073253–4/K 03/2006

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–178 Variation AA.

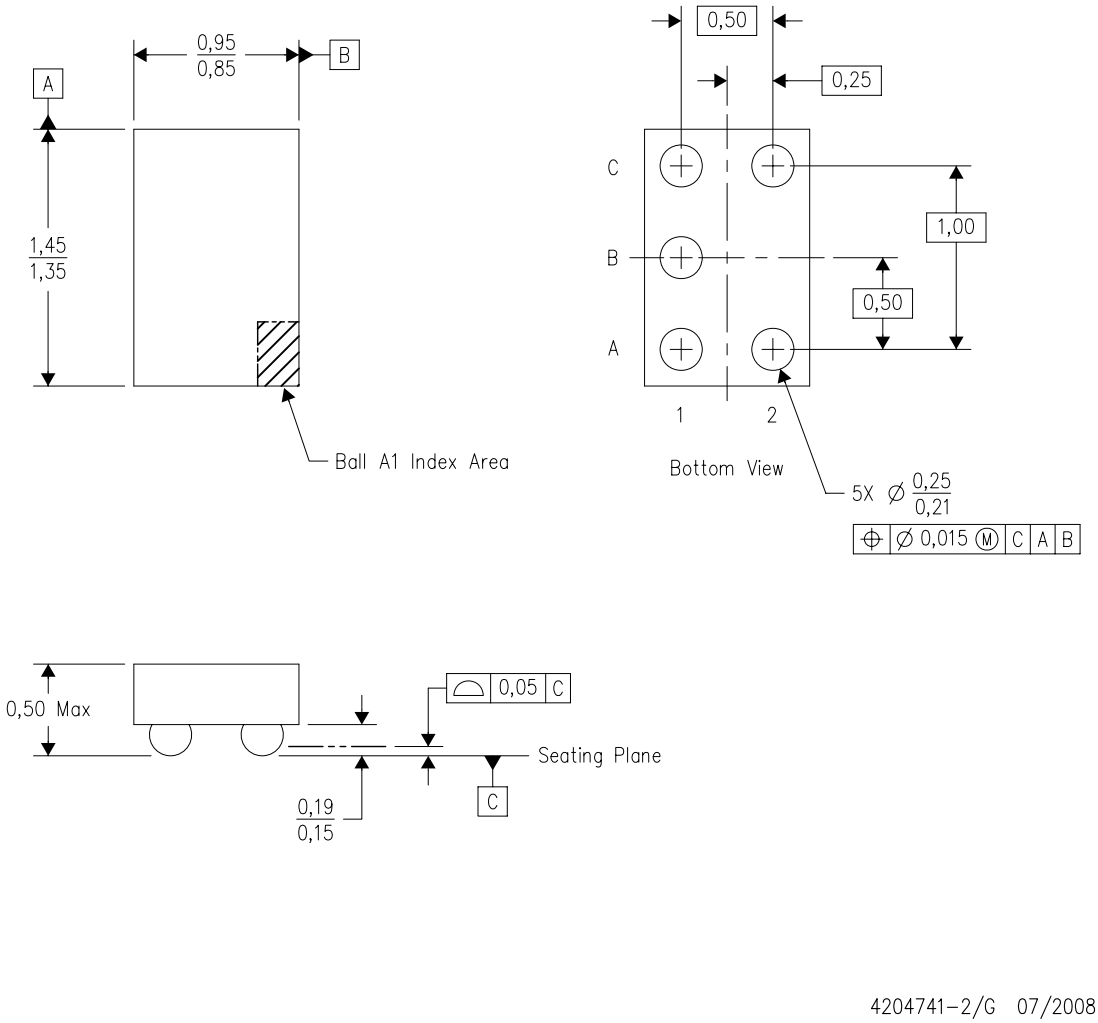
DCK (R–PDSO–G5) PLASTIC SMALL–OUTLINE PACKAGE



4093553–3/G 01/2007

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–203 variation AA.

YZP (R–XBGA–N5) DIE–SIZE BALL GRID ARRAY



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. NanoFree™ package configuration.
D. This package is lead–free. Refer to the 5 YEP package (drawing 4204725) for tin–lead (SnPb).

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